



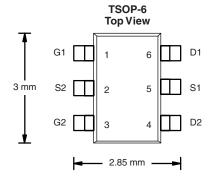
N- and P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
	V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
N-Channel	30	0.105 at V _{GS} = 10 V	2.5		
		0.175 at V _{GS} = 4.5 V	2.0		
P-Channel	- 30	0.200 at V _{GS} = - 10 V	- 1.8		
		0.360 at V _{GS} = - 4.5 V	- 1.2		

FEATURES

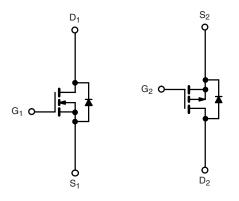
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si3552DV -T1-E3 (Lead (Pb)-free)

Si3552DV-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATING	GS T _A = 25 °	°C, unless other	wise noted			
Parameter		Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage		V _{DS}	30	- 30	V	
Gate-Source Voltage		V _{GS}	± 20	± 20		
O	T _A = 25 °C	I _D	2.5	- 1.8	•	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C		2.0	- 1.2		
Pulsed Drain Current		I _{DM}	8	- 7	А	
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	1.05	- 1.05		
	T _A = 25 °C	D		15	14/	
Maximum Power Dissipation ^{a, b} $T_A = 70 ^{\circ}C$		- P _D	0.73		W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 5 s	- R _{thJA}	93	110		
	Steady State		130	150	°C/W	
Maximum Junction-to-Lead	Steady State	R _{thJL}	75	90		

Notes

a. Surface Mounted on FR4 board.

 $b.\ t \leq 5\ s.$

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Тур.	Max.	Unit	
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	N-Ch	1.0			V	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 1.0				
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	N-Ch			± 100	nA	
date body Loundge	.033		P-Ch			± 100	1171	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V	N-Ch			1		
		V _{DS} = - 24 V, V _{GS} = 0 V	P-Ch			- 1	μΑ	
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	N-Ch			5		
		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	P-Ch	P-Ch				
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	N-Ch	5			A	
	-D(011)	V _{DS} = - 5 V, V _{GS} = - 10 V	P-Ch	- 5			/1	
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, I_D = 2.5 \text{ A}$	N-Ch		0.085			
	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 1.8 A	P-Ch		0.165	0.200	Ω	
Diain-Source On-State Hesistance	DS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 2.0 \text{ A}$	N-Ch		0.140	0.175	32	
		$V_{GS} = -4.5 \text{ V}, I_D = -1.2 \text{ A}$	P-Ch		0.298	0.360		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 2.5 \text{ A}$	N-Ch		4.3		S	
r of ward Transconductance		V _{DS} = - 15 V, I _D = - 1.8 A	P-Ch		2.4			
Diode Forward Voltage ^a	V _{SD}	I _S = 1.05 A, V _{GS} = 0 V	N-Ch		0.81	1.10	V	
blode i di ward voltage		I _S = - 1.05 A, V _{GS} = 0 V	P-Ch		- 0.83 - 1.10		•	
Dynamic ^b								
Total Gate Charge	Q _q	N-Channel	N-Ch		2.1	3.2		
	u g	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 1.8 \text{ A}$	P-Ch		2.4	3.6	nC	
Gate-Source Charge Gate-Drain Charge	Q _{gs}		N-Ch P-Ch		0.7			
		P-Channel	N-Ch		0.9			
		$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -1.8 \text{ A}$	P-Ch		0.7			
	R_g		N-Ch	0.5		2.4	_	
Gate Resistance			P-Ch	3		11	Ω	
Turn-On Delay Time	t _{d(on)}		N-Ch		7	11		
Turn-On Delay Time		N-Channel $V_{DD} = 15 \text{ V}, R_L = 15 \Omega$	P-Ch		8	12	-	
Rise Time	t _r	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_a = 6 \Omega$	N-Ch		9	14		
		- D = 174, rGEN 10 1, r.g 0 ==	P-Ch		12	18		
Turn-Off Delay Time	t _{d(off)}	P-Channel	N-Ch P-Ch		13 12	20 18	ns	
Fall Time	t _f	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$	N-Ch		5	8	-	
		$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω	P-Ch		7	11		
	t _{rr}	I _F = 1.05 A, dl/dt = 100 A/μs	N-Ch		35	60	1	
Source-Drain Reverse Recovery Time		I _F = - 1.05 A, dl/dt = 100 A/μs	P-Ch		30	60		

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

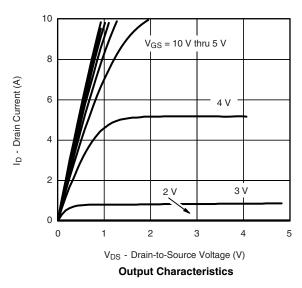
a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

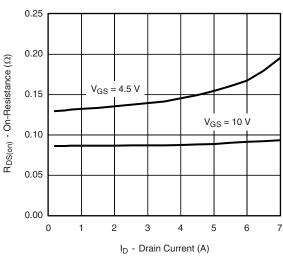


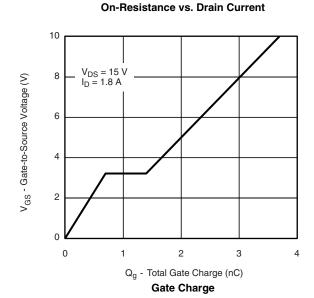


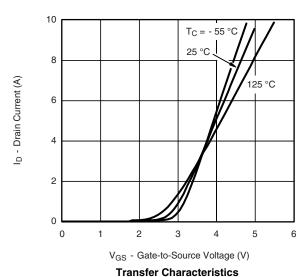


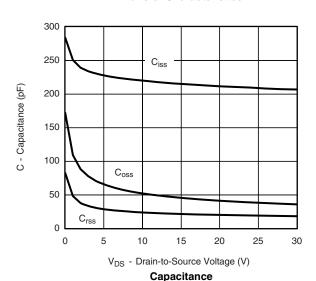
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

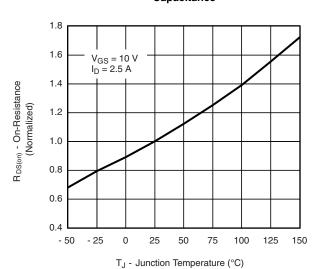










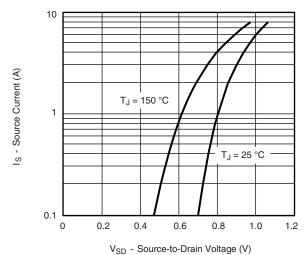


On-Resistance vs. Junction Temperature

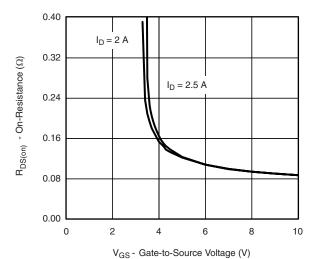
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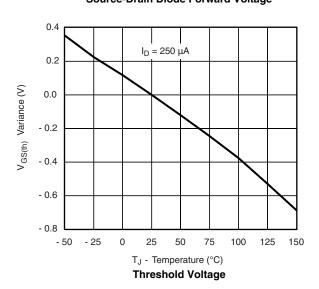
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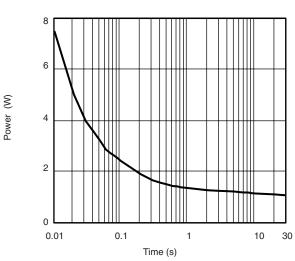


Source-Drain Diode Forward Voltage

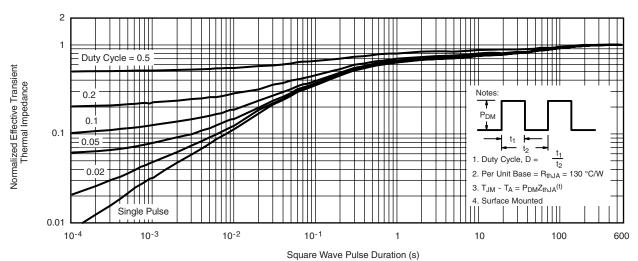


On-Resistance vs. Gate-to-Source Voltage





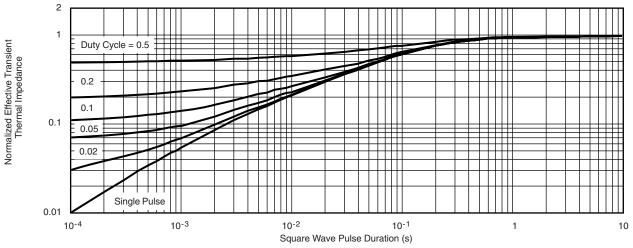
Single Pulse Power (Junction-to-Ambient)



Normalized Thermal Transient Impedance, Junction-to-Ambient

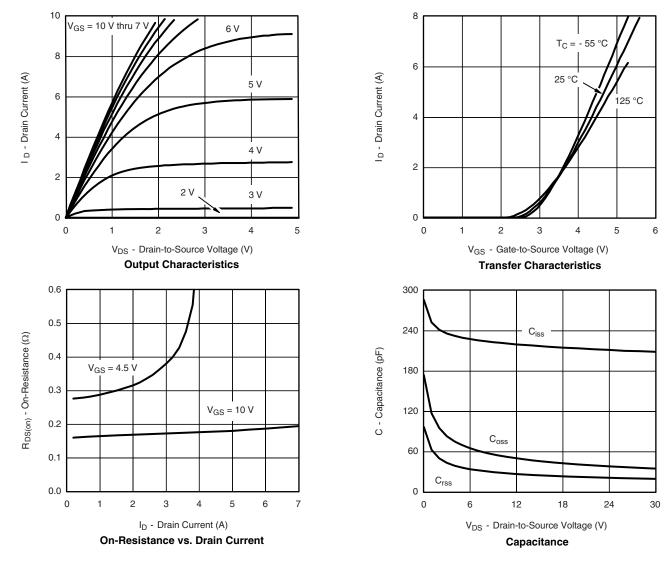


N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

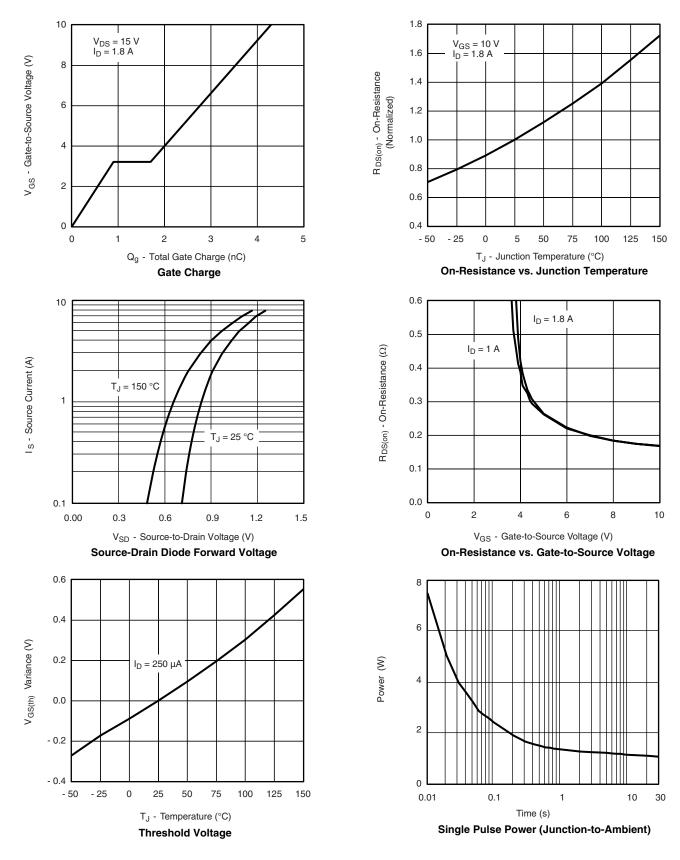


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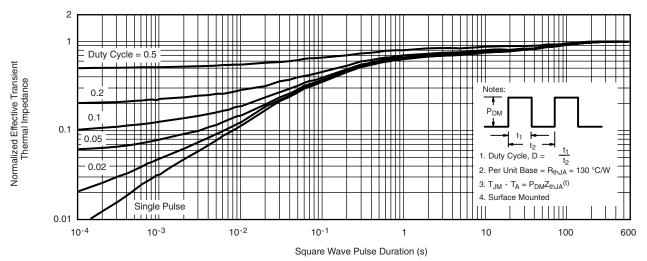
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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

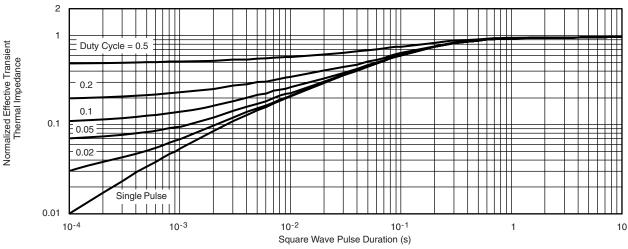




P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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